

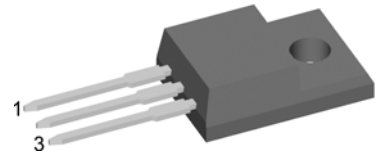
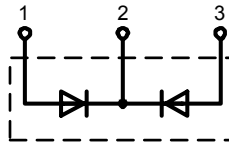
HiPerFRED

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

$V_{RRM} = 200\text{ V}$
 $I_{FAV} = 2 \times 10\text{ A}$
 $t_{rr} = 35\text{ ns}$

Part number (Marking on product)

DPG 20 C 200PN



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{RM} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- TO-220FPAB
- Industry standard outline
 - Plastic overmolded tab for electrical isolation
 - Epoxy meets UL 94V-0
 - RoHS compliant

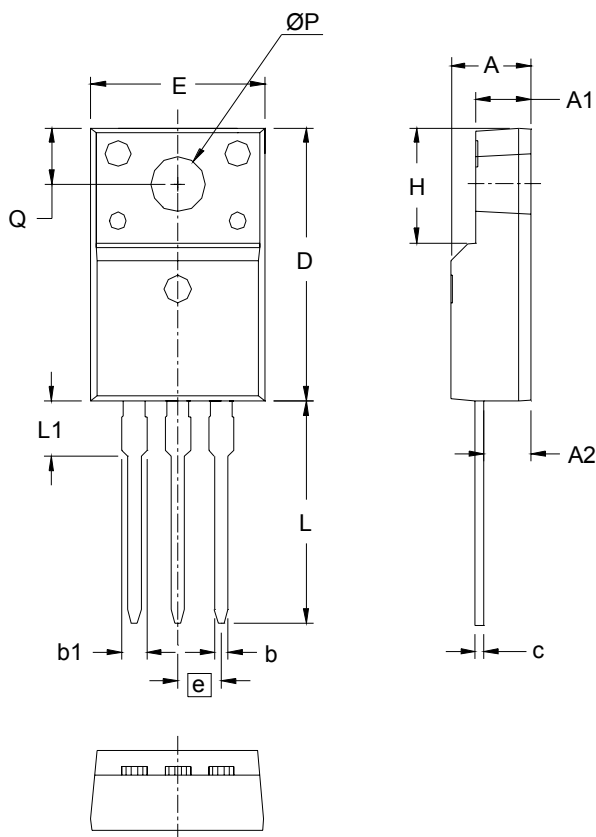
Ratings

Symbol	Definition	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25\text{ °C}$			200	V	
I_R	reverse current	$V_R = 200\text{ V}$			1	μA	
		$V_R = 200\text{ V}$			0.06	mA	
V_F	forward voltage	$I_F = 10\text{ A}$			1.27	V	
		$I_F = 20\text{ A}$			1.45	V	
		$I_F = 10\text{ A}$	$T_{VJ} = 150\text{ °C}$			0.98	V
		$I_F = 20\text{ A}$	$T_{VJ} = 150\text{ °C}$			1.17	V
I_{FAV}	average forward current	rectangular, $d = 0.5$			10	A	
V_{FO}	threshold voltage	} for power loss calculation only			0.69	V	
r_F	slope resistance				22.8	m Ω	
R_{thJC}	thermal resistance junction to case				4.40	K/W	
T_{VJ}	virtual junction temperature		-55		175	$^{\circ}\text{C}$	
P_{tot}	total power dissipation	$T_C = 25\text{ °C}$			65	W	
I_{FSM}	max. forward surge current	$t_p = 10\text{ ms (50 Hz), sine}$			100	A	
I_{RM}	max. reverse recovery current	$I_F = 10\text{ A};$		3		A	
		$-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 125\text{ °C}$			A	
t_{rr}	reverse recovery time	$V_R = 100\text{ V}$		35		ns	
			$T_{VJ} = 125\text{ °C}$			ns	
C_J	junction capacitance	$V_R = 100\text{ V}; f = 1\text{ MHz}$				pF	
E_{AS}	non-repetitive avalanche energy	$I_{AS} = \text{ A}; L = 100\text{ }\mu\text{H}$			tbd	mJ	
I_{AR}	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ.; $f = 10\text{ kHz}$			tbd	A	

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per pin*			35	A
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N
T_{stg}	storage temperature		-55		150	°C
Weight				2		g

* Irms is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Outlines TO-220FPAB


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40